

isc N-Channel MOSFET Transistor

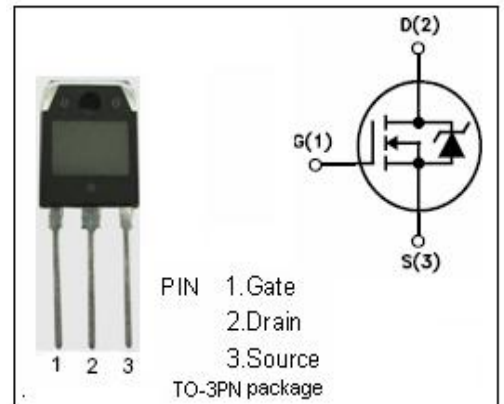
2SK1172

DESCRIPTION

- Drain Current $-I_D=3.5A @ T_C=25^\circ C$
- Drain Source Voltage-
: $V_{DSS}=900V(\text{Min})$

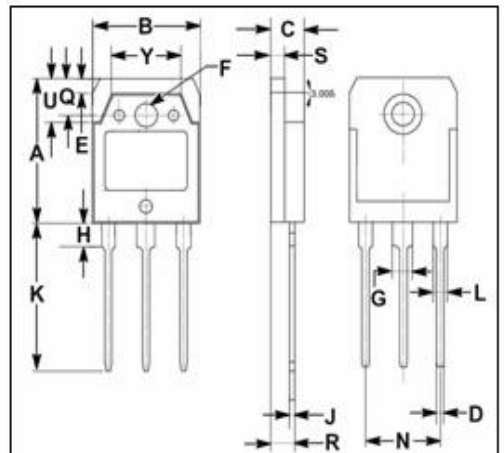
APPLICATIONS

- Designed for high voltage, high speed power switching



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	900	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous@ $T_C=25^\circ C$	3.5	A
P_{tot}	Total Dissipation@ $T_C=25^\circ C$	80	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.10
H	3.20	3.40
J	0.595	0.605
K	20.50	20.70
L	1.90	2.10
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	1.56	$^\circ C/W$
$R_{th\ j-a}$	Thermal Resistance,Junction to Ambient	35	$^\circ C/W$

isc N-Channel Mosfet Transistor**2SK1172****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 1mA	900			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =1mA	2.5	3.5	5.0	V
R _{DS(on)}	Drain-Source On-stage Resistance	V _{GS} =10V; I _D = 2A		4.0	5.5	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =900V; V _{GS} = 0			500	uA
V _{SD}	Forward On-Voltage	I _S =3.5A; V _{GS} =0		0.9	1.35	V
ton	Turn-on time	V _{GS} =10V; I _D =4A; R _L =25 Ω		95	145	ns
toff	Turn-off time			170	255	ns